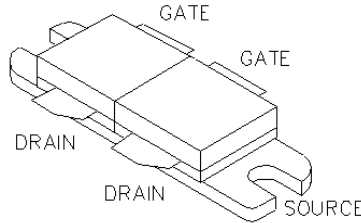




**General Description**

Silicon VDMOS and LDMOS transistors designed specifically for broadband RF applications. Suitable for Military Radios, Cellular and Paging Amplifier Base Stations, Broadcast FM/AM, MRI, Laser Driver and others. "Polyfet"™ process features gold metal for greatly extended lifetime. Low output capacitance and high  $F_t$  enhance broadband performance



**PATENTED GOLD METALIZED SILICON GATE ENHANCEMENT MODE RF POWER VDMOS TRANSISTOR**

**300 Watts Gemini**

**Package Style AR**

**HIGH EFFICIENCY, LINEAR, HIGH GAIN, LOW NOISE**

**ABSOLUTE MAXIMUM RATINGS (TC = 25 °C)**

Total Device Dissipation	Junction to Case Thermal Resistance	Maximum Junction Temperature	Storage Temperature	DC Drain Current	Drain to Gate Voltage	Drain to Source Voltage	Gate to Source Voltage
500 Watts	0.35 °C/W	200 °C	-65 °C to 150 °C	24 A	150 V	150 V	30V

**RF CHARACTERISTICS ( 300 WATTS OUTPUT )**

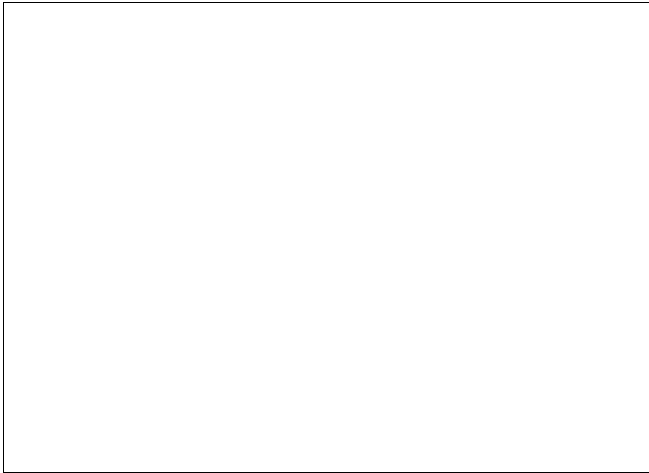
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Gps	Common Source Power Gain	13			dB	$I_{dq} = 1.2 \text{ A}, V_{ds} = 50.0 \text{ V}, F = 150 \text{ MHz}$
n	Drain Efficiency		65		%	$I_{dq} = 1.2 \text{ A}, V_{ds} = 50.0 \text{ V}, F = 150 \text{ MHz}$
VSWR	Load Mismatch Tolerance			20:1	Relative	$I_{dq} = 1.2 \text{ A}, V_{ds} = 50.0 \text{ V}, F = 150 \text{ MHz}$

**ELECTRICAL CHARACTERISTICS (EACH SIDE)**

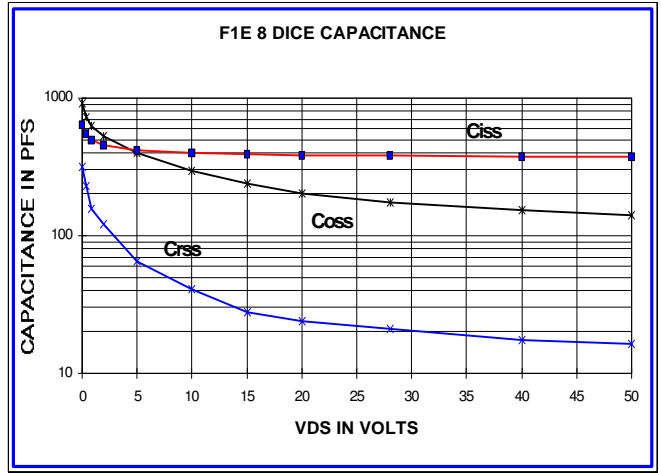
SYMBOL	PARAMETER	MIN	TYP	MAX	UNITS	TEST CONDITIONS
Bvdss	Drain Breakdown Voltage	125			V	$I_{ds} = 0.1 \text{ A}, V_{gs} = 0 \text{ V}$
Idss	Zero Bias Drain Current			16	mA	$V_{ds} = 50.0 \text{ V}, V_{gs} = 0 \text{ V}$
Igss	Gate Leakage Current			1	uA	$V_{ds} = 0 \text{ V}, V_{gs} = 30 \text{ V}$
Vgs	Gate Bias for Drain Current	1		7	V	$I_{ds} = 0.15 \text{ A}, V_{gs} = V_{ds}$
gM	Forward Transconductance		6.4		Mho	$V_{ds} = 10 \text{ V}, V_{gs} = 5 \text{ V}$
Rdson	Saturation Resistance		0.18		Ohm	$V_{gs} = 20 \text{ V}, I_{ds} = 16 \text{ A}$
Idsat	Saturation Current		38.4		Amp	$V_{gs} = 20 \text{ V}, V_{ds} = 10 \text{ V}$
Ciss	Common Source Input Capacitance		360		pF	$V_{ds} = 50.0 \text{ V}, V_{as} = 0 \text{ V}, F = 1 \text{ MHz}$
Crss	Common Source Feedback Capacitance		17.6		pF	$V_{ds} = 50.0 \text{ V}, V_{as} = 0 \text{ V}, F = 1 \text{ MHz}$
Coss	Common Source Output Capacitance		160		pF	$V_{ds} = 50.0 \text{ V}, V_{as} = 0 \text{ V}, F = 1 \text{ MHz}$

# F1430

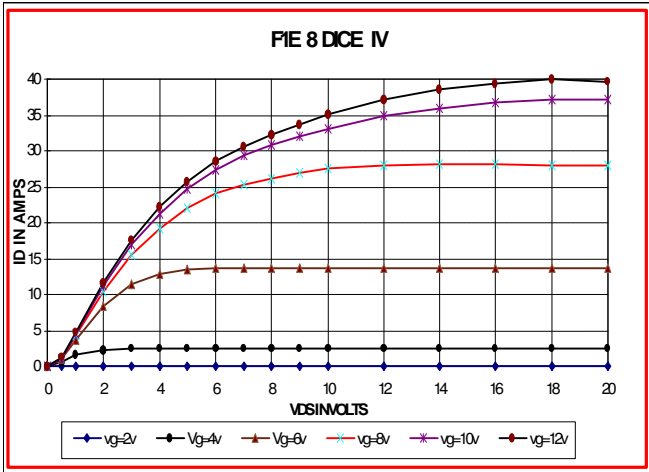
POUT VS PIN GRAPH



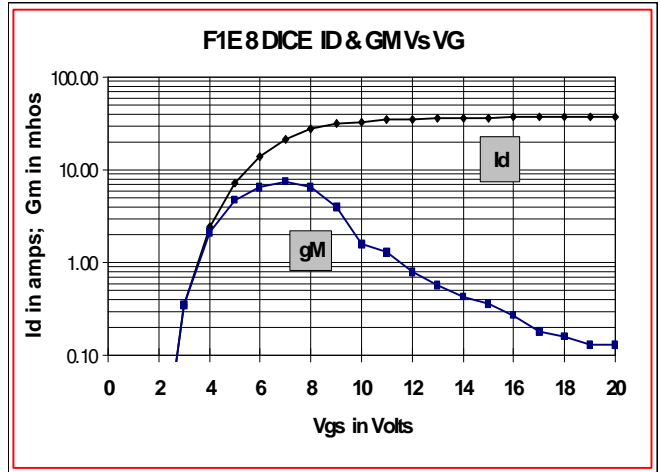
CAPACITANCE VS VOLTAGE



IV CURVE



ID AND GM VS VGS



S11 AND S22 SMITH CHART



PACKAGE DIMENSIONS IN INCHES

